

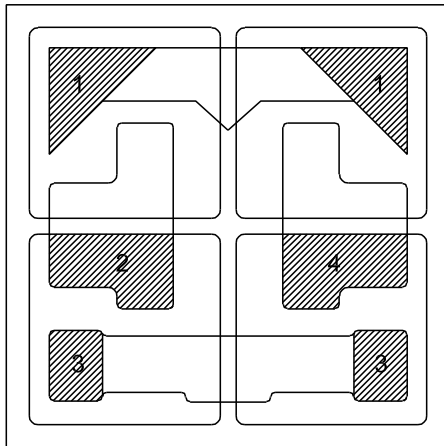
**PROCESS CPD73**  
**Bridge Rectifier**  
Monolithic Quad Diode Bridge Chip



**PROCESS DETAILS**

Die Size	25 x 25 MILS
Die Thickness	6.0 MILS
Bonding Pad Area 1 (+DC)	3.0 x 3.0 MILS
Bonding Pad Area 2 (AC)	3.0 x 7.0 MILS
Bonding Pad Area 3 (-DC)	3.0 x 4.0 MILS
Bonding Pad Area 4 (AC)	3.0 x 7.0 MILS
Top Side Metalization	Al - 12,000Å
Back Side Metalization	Au - 5,000Å

**GEOMETRY**



R1

**GROSS DIE PER 3 INCH WAFER**

10,000

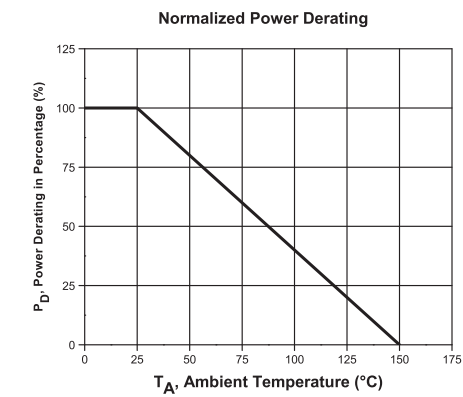
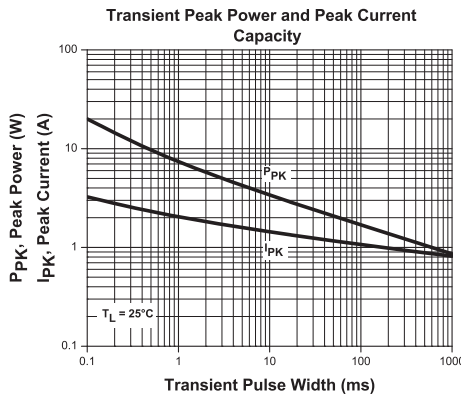
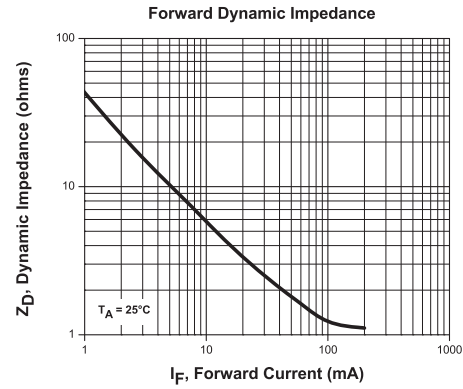
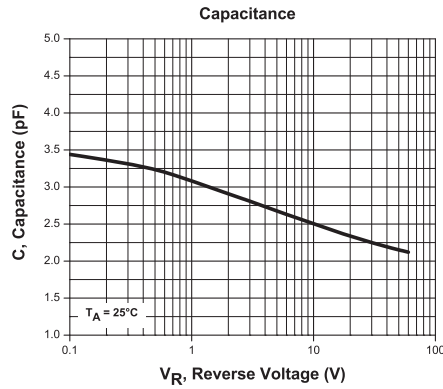
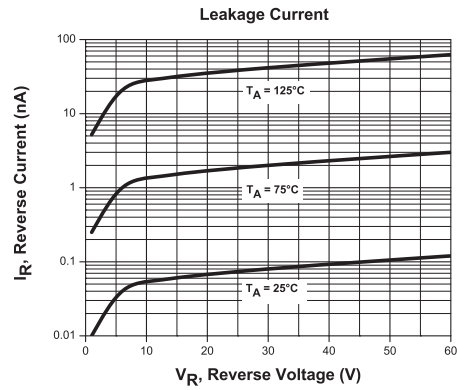
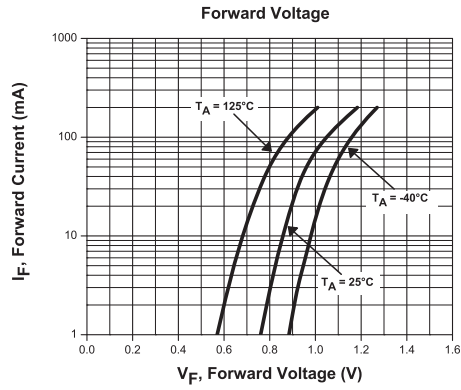
**PRINCIPAL DEVICE TYPES**

CMFBR-6F

R2 (22-March 2010)

# PROCESS CPD73

## Typical Electrical Characteristics



R2 (22-March 2010)